31. (Amended) A capacitor structure in an integrated circuit, the structure comprising:

a supporting structure;

a conductive layer situated on a surface of the supporting structure;

a layer of conductive metallic oxide having a pitted surface situated on the conductive layer; and

a layer of dielectric material disposed conformally on the pitted surface.

42. (Amended) An integrated circuit, comprising a plurality of capacitors that include a conductive layer, a layer of conductive metallic oxide having a pitted surface situated on the conductive layer, and a layer of dielectric material disposed conformally on the pitted surface.

Please add the following new claims:

43. (New) An enhanced-surface-area conductive structure in an integrated circuit, the structure comprising a conductive layer with at least one surface having a plurality of pits, wherein the pits are associated with a ruthenium phase in the conductive layer.

44. (New) A capacitor structure in an integrated circuit, comprising:

a layer of conductive metallic oxide with a surface having a plurality of pits associated with a metallic phase in the conductive layer; and

a layer of dielectric material disposed conformally on the pitted surface.

45. (New) A capacitor structure in an integrated circuit, the structure comprising:

a supporting structure;

a layer of conductive metallic oxide having a surface that includes a plurality of pits associated with a metallic phase in the conductive metallic oxide layer; and

a layer of dielectric material disposed conformally on the pitted surface.

46. (New) The capacitor structure of claim 45, further comprising a continuous layer of conductive material disposed on the layer of dielectric material.

47. (New) The capacitor structure of claim 45, wherein at least some of the pits in the surface of the conductive metallic oxide layer extend completely through the conductive metallic oxide layer.

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48. (New) The capacitor structure of claim 45, wherein the pits in the surface of the conductive metallic oxide layer have a mean diameter in the range of one to three times a thickness of the conductive metallic oxide layer.

49. (New) The capacitor structure of claim 45, wherein the pits in the surface have a mean closest distance that is at least two times a thickness of the layer of dielectric material.

50. (New) The capacitor structure of claim 45, wherein the conductive metallic oxide layer comprises ruthenium oxide.

REMARKS

Reconsideration of the subject application is requested in view of the preceding amendments and the following remarks. By this amendment, claims 30, 31, and 42 are amended and new claims 43-50 are submitted for consideration. Upon entry of this Amendment, claims 30-50 are in the application.

Support for new claims 43-50 can be found at in the specification at, for example, claims 31-36 as filed, Figures 1-5, and page 5, line 11 through page 7, line 5. No new matter is introduced.

Claims 30-33 and 36-42 stand rejected as allegedly anticipated by Derderian et al, U.S. Patent 6,188,097 ("Derderian"). This rejection is traversed. Claim 30 as amended recites an enhanced-surface-area conductive structure in an integrated circuit. The structure comprises a supporting structure, a conductive layer situated on a surface of the supporting structure, and a